

## 1 Scope

The present specifications shall apply to Sanken silicon diode, FMC-26UA.

## 2 Outline

Type	Silicon Rectifier Diode	
Structure	Resin Molded	Flammability: UL94V-0 (Equivalent)
Applications	High Frequency Rectification, etc.	

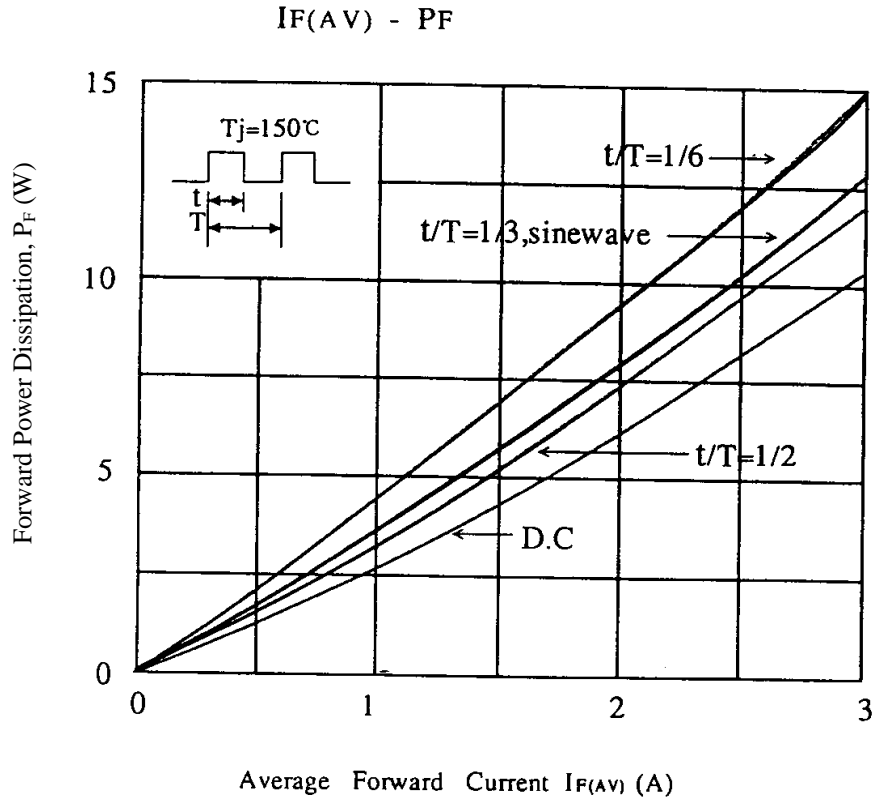
## 3 Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	$V_{RSM}$	V	1200	
2	Peak Reverse Voltage	$V_{RM}$	V	1200	
3	Average Forward Current	$I_{F(AV)}$	A	3.0	$T_c=98^\circ\text{C}$ , sinewave
4	Peak Surge Forward Current	$I_{FSM}$	A	50	10ms Half sinewave, one shot
5	$I^2t$ Limiting Value	$I^2t$	$\text{A}^2\text{s}$	12.5	
6	Junction Temperature	$T_j$	$^\circ\text{C}$	-40 to +150	
7	Storage Temperature	$T_{stg}$	$^\circ\text{C}$	-40 to +150	
8	Screwing Torque		$\text{N}\cdot\text{m}$	0.59	
9	Dielectric Strength		kV	A.C. 1.0	Junction and case (1min.)

4 Electrical characteristics ( $T_a=25^\circ\text{C}$  , unless otherwise specified)

No.	Item	Symbol	Unit	Rating	Conditions
1	Forward Voltage Drop	$V_F$	V	4.0 max.	$I_F=3.0\text{A}$
2	Reverse Leakage Current	$I_R$	$\mu\text{A}$	500 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H\cdot I_R$	mA	3 max.	$V_R=V_{RM}$ , $T_j=150^\circ\text{C}$
4	Reverse Recovery Time	trr1	ns	70 max.	$I_F=I_{RP}=500\text{mA}$ 90% Recovery point, $T_j=25^\circ\text{C}$
		trr2	ns	35 max.	$I_F=0.5\text{A}$ , $I_{RP}=1\text{A}$ 75% Recovery point, $T_j=25^\circ\text{C}$
5	Thermal Resistance	$R_{th(j-c)}$	$^\circ\text{C}/\text{W}$	4.0 max.	Between Junction and case

5 Characteristics



6 Derating

